SSC80313GN2

P-Channel Enhancement Mode MOSFET

➢ Features

V_{DS}	V_{GS}	$R_{DS(ON)}$	I_D
-30V	±20V	22mΩ@-10V	-8A
		29mΩ@-4V5	

➢ Description

This device is produced with high cell density DMOS trench technology, which is especially used to minimize on-state resistance. This device particularly suits low voltage applications such as portable equipment, power management and other battery powered circuits, and low in-line power dissipation are needed in a very small outline surface mount package.

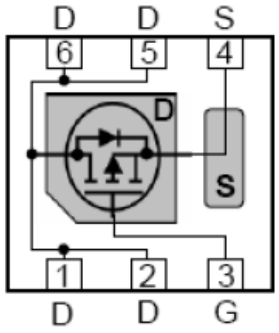
➢ Applications

- Load Switch
- Portable Devices
- DCDC Conversion
- Charging

➢ Ordering Information

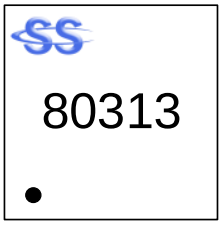
Device	Package	Shipping
SSC80313GN2	DFN2020-6L	3000/Reel

➢ Pin Configuration



DFN2020-6L (Top View)

Bottom View



Marking

➢ Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter		Ratings	Unit
V_{DS}	Drain-to-Source Voltage		-30	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current [d]	T_C=25℃	-8	A
		T_C=100℃	-6	
I_{DM}	Pulsed Drain Current [b]		-35	A
P_D	Power Dissipation [c]	T_C=25℃	3.1	W
		T_C=100℃	1.2	
T_J	Operation junction temperature		-55~150	℃
T_{STG}	Storage temperature range		-55~150	

➢ Thermal Resistance Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance [a]	40	℃/W

Note:

a. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in^2 FR-4 board with 2oz.copper, in a still air environment with T_A=25℃.The value in any given application depends on the user is specific board design. The power dissipation is based on the t≤10s thermal resistance rating.

b. Repetitive rating, pulse width limited by junction temperature.

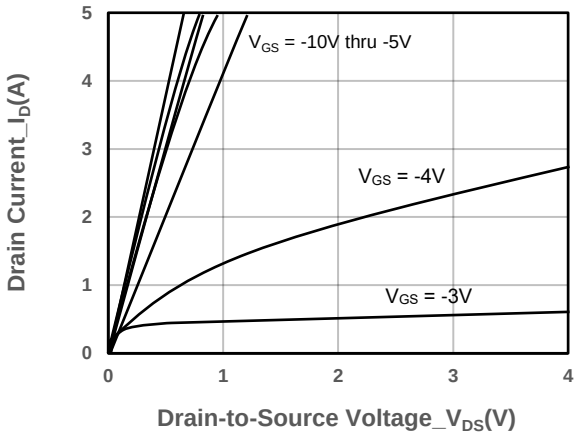
c. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.

d. The maximum current rating is package limited.

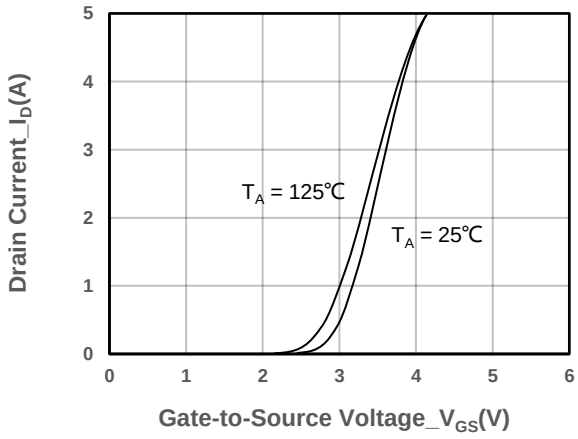
➢ Electrical Characteristics (T_A=25℃ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D =- 250uA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250uA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -7A		22	28	mΩ
		V_{GS} = -4.5V, I_D = -4A		29	38	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -30V, V_{GS} = 0V			-1	μA
Gate-Source Leak Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
Forward Voltage	V_{SD}	V_{GS} = 0V, I_S = -2A			-1.3	V
Gate Resistance	R_G	V_{DS} = 0V, f = 1MHz		11		Ω
Input Capacitance	C_{ISS}	V_{DS} = -15V, V_{GS} = 0V, f = 1MHz		890		pF
Output Capacitance	C_{OSS}			110		
Reverse Transfer Capacitance	C_{RSS}			90		
Total Gate Charge	Q_G	V_{GS} = -10V, V_{DS} = -20V, I_D =-5A		15		nC
Gate to Source Charge	Q_{GS}			5		
Gate to Drain Charge	Q_{GD}			6		
Turn-on Delay Time	$T_{D(ON)}$	V_{GS} = -10V, V_{DS} = -20V, R_L = 1Ω, R_G = 3Ω		11		ns
Rise Time	T_r			20		
Turn-off Delay Time	$T_{D(OFF)}$			35		
Fall Time	T_f			21		
Reverse Recovery Time	T_{rr}	I_F= -10A, dI/dt=100A/μs		20		ns
Reverse Recovery Charge	Q_{rr}	I_F= -10A, dI/dt=100A/μs		8		nC

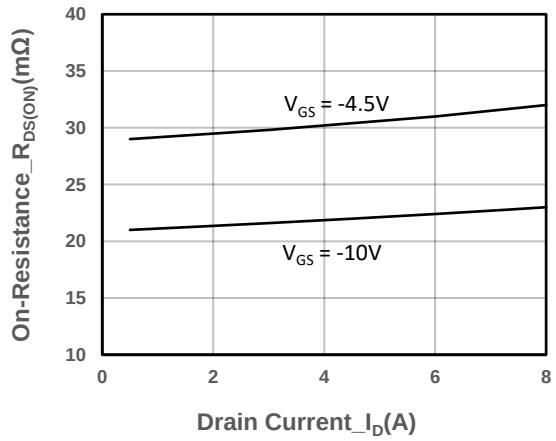
➢ Typical Performance Characteristics (T_A=25℃ unless otherwise noted)



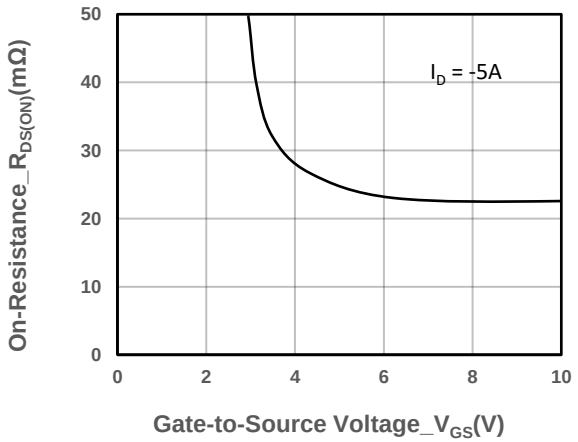
Output Characteristics



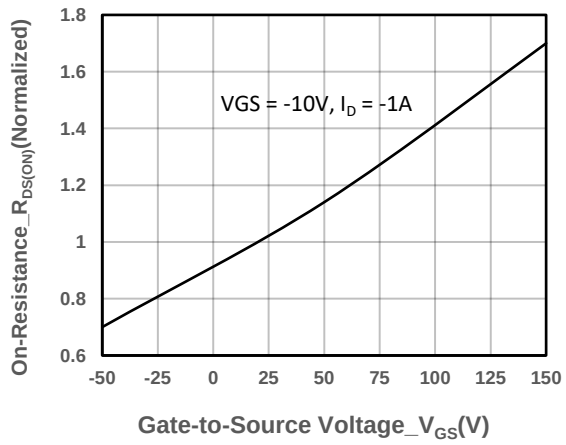
Transfer Characteristics



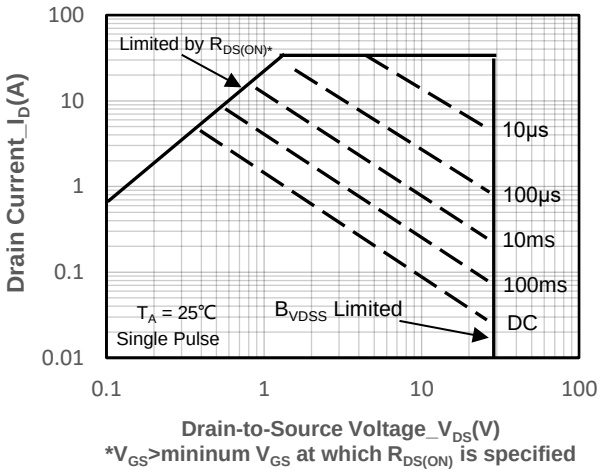
On-Resistance vs. Drain Current and Gate Voltag



On-Resistance vs. Gate-to-Source Voltage

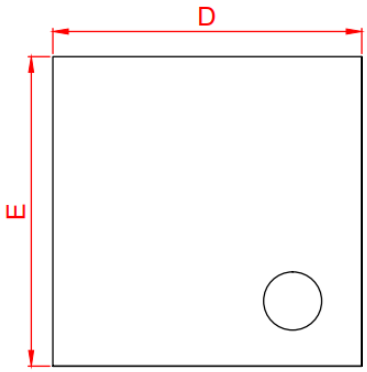


On-Resistance vs. Junction Temperature

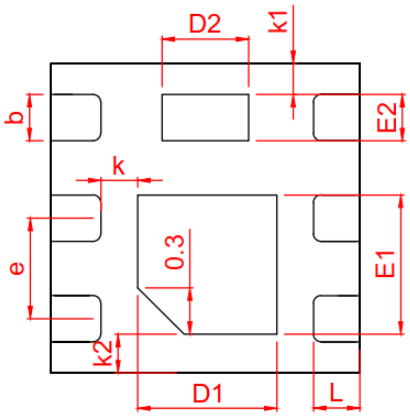


Safe Operating Area vs. Junction-to-Ambient

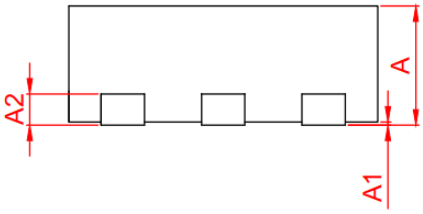
➢ Package Information



TOP VIEW



BOTTOM VIEW



SIDE VIEW

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.50	0.55	0.60
* A1	0.00	0.02	0.05
* b	0.25	0.30	0.35
* A2	0.152 BSC		
* D	1.95	2.00	2.05
* E	1.95	2.00	2.05
* E1	0.80	0.90	1.00
* E2	0.25	0.30	0.35
* D1	0.80	0.90	1.00
* D2	0.46	0.56	0.66
* e	0.65 REF		
* L	0.25	0.30	0.35
* K	0.20	0.25	0.30
* K1	0.15	0.20	0.25
* K2	0.20	0.25	0.30

DISCLAIMER

SSCSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. SSCSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICIENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.